

PRODUCT/PROCESS CHANGE NOTIFICATION

PCN MPA-PWR/06/2192 Notification Date 12/13/2006

New Assembly/Testing Location SOT32 package for Power Bipolar in CDIL Subcontractor

PWR - PWR BIP/ IGBT/ RF

Product Identification (Product Family/Commercial Product)	Power Bipolar
Type of change	Package assembly location change
Reason for change	Service improvement / capability extension
Description of the change	Power Bipolar Division has decided to use Cdil subcontractor for the devices reported in the enclosed list (in addition to the part numbers already in production since year 2002). This change will assure an additional assembly/testing location that will be translate in a better service for our Customers. The SOT32 package coming from CDIL subcontractor is perfectly compatible with SOT32 package currently in use for the same products (flat lead shape version). This will not change the guaranteed electrical characteristics. Samples are available for lines used for Subcontractor qualification.
Product Line(s) and/or Part Number(s)	See attached
Description of the Qualification Plan	See attached
Change Product Identification	"JB" as Production area code on package
Manufacturing Location(s)	

Table 1. Change Identification

Table 2. Change Implementation Schedule

Forecasted implementation date for change	13-Mar-2007
Forecasted availabillity date of samples for customer	05-Dec-2006
Forecasted date for STMicroelectronics change Qualification Plan results availability	05-Dec-2006
Estimated date of changed product first shipment	13-Mar-2007

Table 3. Change Responsibility

	Name	Signature	Date
Division Product Manager	Claudio Porto		Dec.05 ,06
Division Q.A. Manager	Giuseppe Falcone		Dec.05 ,06
Division Marketing Manager	Alfio Lanzafame		Dec.05 ,06

Table 4. List of Attachments

Customer Part numbers list	
Qualification Plan results	

	>
Customer Acknowledgement of Receipt	PCN MPA-PWR/06/2192
Please sign and return to STMicroelectronics S	Sales Office Notification Date 12/13/2006
Qualification Plan Denied	Name:
Qualification Plan Approved	Title:
	Company:
Change Denied	Date:
Change Approved	Signature:
Remark	



Reliability evaluation on

SOT-32 Package

for Power Bipolar in CDIL Subcontractor



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Introduction

This report aims at the internal qualification of the SOT-32 Package for Power Bipolar in CDIL Subcontractor.

The Qualification Reliability test trials have been performed in ST Catania Site.

The evaluation results meet ST products qualification targets, therefore the SOT-32 Package for Power Bipolar in CDIL Subcontractor is qualified.

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Test Vehicles:

Product Line	Sales Type	Package
B641	BD238	SOT-32
BG01	BD681	SOT-32
BK01	BD678	SOT-32
F641	BD438	SOT-32

Failure Criteria :

A failed component is a device which becomes inoperative during the test or it fails on meeting the end limits foreseen in the device specification, for one or more than the parameters here below reported

Power BIPOLAR Parameter

Collector Leakage Current (Icbo or Iceo or Ices, etc...) Emitter Leakage (Iebo) HFE, Vcesat, Vbesat, Vf Breakdown Voltage (BVcbo, BVceo,Vbces, Bvebo)

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Reliability Evaluation Plan and results

D.U.T.: BD238

Line: B641

Package: SOT-32

Test	Conditions	S.S.	Requirement	Results
H.T.S.	TA=150℃	77 x 1 Lot	Parameter devia- tion within spec. limits at 1000 hours.	No parameter deviation out of spec. limits at 1000 hours.
T.H.B.	TA=85℃ - RH=85% Vbias= 50V	77 x 1 Lot	Parameter devia- tion within spec. limits at 1000 hours.	No parameter deviation out of spec. limits at 1000 hours.
H.T.R.B.	T.A.= 150℃ Vces = 80 V	77 x 1 Lot	Parameter devia- tion within spec. limits at 1000 hours.	No parameter deviation out of spec. limits at 1000 hours.
PRESSURE POT	TA=121℃ - PA=2Atm	77 x 1 Lot	Parameter devia- tion within spec. limits at 96 hours.	No parameter deviation out of spec. limits at 96 hours.
THERMAL FATIGUE	∆TC=105 ℃ - Pd= 3W	77x1 Lot	Parameter devia- tion within spec. limits at 10k cy- cles.	No failure up to 10Kcy.
THERMAL CYCLES AIR TO AIR	TA=-65℃ TO 150℃ 1 HOUR / CYCLE	77 x 1 Lot	Parameter devia- tion within spec. limits at 500 cy- cles.	No parameter deviation out of spec. limits at 500 cy

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Reliability Evaluation Plan and results

D.U.T.: BD681

Line: BG01

Package: SOT-32

Test	Conditions	S.S.	Requirement	Results
H.T.S.	TA=150℃	77 x 1 Lot	Parameter devia- tion within spec. limits at 1000 hours.	No parameter deviation out of spec. limits at 1000 hours.
T.H.B.	TA=85℃ - RH=85% Vbias= 50V	77 x 1 Lot	Parameter devia- tion within spec. limits at 1000 hours.	No parameter deviation out of spec. limits at 1000 hours.
H.T.R.B.	T.A.= 150℃ Vces = 80 V	77 x 1 Lot	Parameter devia- tion within spec. limits at 1000 hours.	No parameter deviation out of spec. limits at 1000 hours.
PRESSURE POT	TA=121℃ - PA=2Atm	77 x 1 Lot	Parameter devia- tion within spec. limits at 96 hours.	No parameter deviation out of spec. limits at 96 hours.
THERMAL FATIGUE	∆TC=105 ℃ - Pd= 3W	77x1 Lot	Parameter devia- tion within spec. limits at 10k cy- cles.	No failure up to 10Kcy.
THERMAL CYCLES AIR TO AIR	TA=-65℃ TO 150℃ 1 HOUR / CYCLE	77 x 1 Lot	Parameter devia- tion within spec. limits at 500 cy- cles.	No parameter deviation out of spec. limits at 500 cy

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PACKAGE: SOT-32

Reliability Evaluation Plan and results

D.U.T. : BD678 LINE: BK01

Conditions S.S. Requirement Test Results Parameter devia-No parameter deviation 77 x 1 tion within spec. out of spec. limits at 1000 H.T.S. TA=150℃ limits at 1000 hours. Lot hours. Parameter devia-No parameter deviation TA=85℃ - RH=85% 77 x 1 tion within spec. out of spec. limits at 1000 T.H.B. Vbias= 50V Lot limits at 1000 hours. hours. Parameter devia-No parameter deviation T.A.= 150℃ 77 x 1 tion within spec. out of spec. limits at 1000 H.T.R.B. limits at 1000 hours. Vces = 48 V Lot hours. Parameter devia-No parameter deviation Ta=121℃:Pa=2Atm out of spec. limits at 96 77 x 1 tion within spec. PRESSURE POT limits at hours. Lot 96 hours. Parameter devia-No failure up to 10Kcy. THERMAL FATIGUE 77x1 tion within spec. ∆TC=105 ℃ - Pd= 3W limits at 10k cy-Lot cles. Parameter devia-No parameter deviation Ta=-65 ℃ to +150℃; 77 x 1 tion within spec. out of spec. limits at 500 THERMAL CYCLES 1 hour/cycle Lot limits at 500 cy-AIR TO AIR су cles.

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PACKAGE: SOT-32

Reliability Evaluation Plan and results

D.U.T. : BD438 LINE: F641

Conditions S.S. Requirement Test Results Parameter devia-No parameter deviation TA=150℃ 77 x 1 tion within spec. out of spec. limits at 1000 H.T.S. limits at 1000 hours. Lot hours. Parameter devia-No parameter deviation TA=85℃ - RH=85% 77 x 1 tion within spec. out of spec. limits at 1000 T.H.B. limits at 1000 Vbias= 50V Lot hours. hours. Parameter devia-No parameter deviation T.A.= 150℃ 77 x 1 tion within spec. out of spec. limits at 1000 H.T.R.B. limits at 1000 hours. Vces = 48 V Lot hours. Parameter devia-No parameter deviation Ta=121℃:Pa=2Atm out of spec. limits at 96 77 x 1 tion within spec. PRESSURE POT limits at hours. Lot 96 hours. Parameter devia-No failure up to 10Kcy. THERMAL FATIGUE 77x1 tion within spec. ∆TC=105 ℃ - Pd= 3W limits at 10k cy-Lot cles. Parameter devia-No parameter deviation out of spec. limits at 500 Ta=-65 ℃ to +150℃; 77 x 1 tion within spec. THERMAL CYCLES AIR TO AIR 1 hour/cycle Lot limits at 500 cyсу cles.

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D.U.T.: BD238	Line: B641	Package: SOT-32
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DIE	Technology: Material: Metallization – Front : - Back :	Epitaxial Base PNI Silicon Al Ti/Ni/Au	Passivation : Dimensions :	•
DIE ATTACH	Soft Solder Pb/Sn/Ag	FRAME	Frame and lead material: Frame coating : Lead coating :	Row copper Nickel Plated Sn 100%
WIRE BOND	Ultrasonic	WIRE	Material : Diameter :	Al Base Al Emitter 5 mils Base 5 mils Emitter
SEALING	Molding	PACKAGING	Material :	Epoxy Resin

PRODUCTION PLACES:	WAFER PROCESSING	: SINGAPORE
	ASSEMBLY LOCATION	: INDIA
	Q.A. LOCATION	: INDIA

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DIE	Technology: Material: Metallization – Front : - Back :	Epitaxial Base NPI Silicon Al Ti/Ni/Au	N Passivation : Dimensions :	P-Vapox 90 x 70 mils
DIE ATTACH	Soft Solder Pb/Sn/Ag	FRAME	Frame and lead material: Frame coating : Lead coating :	Row copper Nickel Plated Sn 100%
WIRE BOND	Ultrasonic	WIRE	Material : Diameter :	Al Base Al Emitter 5 mils Base 5 mils Emitter
SEALING	Molding	PACKAGING	Material :	Epoxy Resin

PRODUCTION PLACES:WAFER PROCESSING: SINGAPOREASSEMBLY LOCATION: INDIAQ.A. LOCATION: INDIA



D.U.T. : BD678 LINE: BK01 PACKAGE: SOT-32

DIE		Epitaxial Base PNI Silicon Al/Si Ti-Ni-Au	Passivation : Dimensions :	•
DIE ATTACH	Soft Solder Pb/Sn/Ag	FRAME	Frame and lead material: Frame coating : Lead coating :	Row copper, Nickel Plated Sn 100%
WIRE BOND	Ultrasonic	WIRE	Material : Diameter :	Al Base Al Emitter 5 mils Base 5 mils Emitter
SEALING	Molding	PACKAGING	Material :	Epoxy Resin

PRODUCTION PLACES :	WAFER PROCESSING	: SINGAPORE
	ASSEMBLY LOCATION	: INDIA
	Q.A. LOCATION	: INDIA

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D.U.T. : BD438 LINE: F641 PACKAGE: SOT-32

DIE	Technology: Material: Metallization – Front : - Back :	Epitaxial Base PNF Silicon Al/Si Ti/Ni/Au	Passivation :	P-Vapox 60 x 79 mils
DIE ATTACH	Soft Solder Pb/Sn/Ag	FRAME	Frame and lead material: Frame coating : Lead coating :	Row copper Nickel Plated Sn 100%
WIRE BOND	Ultrasonic	WIRE	Material : Diameter :	Al Base Al Emitter 5 mils Base 5 mils Emitter
SEALING	Molding	PACKAGING	Material :	Epoxy Resin

PRODUCTION PLACES:WAFER PROCESSING: SINGAPOREASSEMBLY LOCATION: INDIAQ.A. LOCATION: INDIA

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Reliability Test Description

High Temperature Reverse Bias (HTRB)

This test is performed in order to demonstrate the quality and reliability of devices subjected to an elevated temperature and simultaneously reverse biased. The purpose of this test is to detect surface defects such as poor passivation, presence of contaminants, etc...

High Temperature Storage (HTS)

This stress test is performed to check the device life in a high temperature ambient. Specimens are put for a period of time inside a stove in free air. Detectable failure mechanisms are presence of contaminants and metal corrosion.

Thermal Cycles/Shocks

The purpose of this test is to determine the resistance of devices to exposure to extreme changes in temperature. Specimens are first placed in a suitable environment at a low temperature and then transferred to one at high temperature. Effects of thermal cycles/shocks include cracking of die, breaking of wire bonding, mechanical damage to the device case.

Temperature Humidity Bias (THB)

This test is performed to check the device life in a high humidity ambient. Specimens are subjected to a permanent bias in a climatic chamber in the presence of steam. Detectable failure mechanisms are metal corrosion and moulding defects.

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Reliability Test Description (continued)

Pressure Pot

This test is performed in order to check device life in a high humidity ambient in an accelerated way. Specimens are subjected for a period of time inside an autoclave in the presence of steam and pressure. Detectable failure mechanism is metal corrosion.

Thermal Fatigue

This test is performed to demonstrate the quality and reliability of devices exposed to cyclic variation in electrical stress between "on" and "off" conditions and resultant cyclic variation in device and case temperatures (thermo-mechanical stress). The purpose of this test is to detect assembly defects : improper die-attach, bonding weakness and thermal mismatch among various components of the package.

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